

## COMPOUND SEMICONDUCTOR OPTOELECTRONIC DEVICE

### ABSTRACT OF THE DISCLOSURE

A method for manufacturing a compound semiconductor  
5 optoelectronic device is proposed. There are steps of : forming an  
optoelectronic device epitaxial wafer, the optoelectronic device epitaxial  
wafer containing a V-shaped pit due to threading dislocation; forming  
an insulated isolation material in the V-shaped pit of the optoelectronic  
device epitaxial wafer; and forming an electrode layer on the  
10 optoelectronic device epitaxial wafer having the insulated isolation  
material in the V-shaped pit for completing the optoelectronic device.